

Please change the Title to PLASMA PRE-TREATMENT TO REMOVE

B1 RESIDUES FORMED IN A VIA.

In the Claims:

Please cancel claims 1-15 and add claims 21-25 as follows:

- Subcl
- B2
21. A method of fabricating an electronic device having a first conductive structure electrically connected to a second conductive structure situated over a semiconductor substrate, said method comprising the steps of:
forming said first conductive structure;
forming an insulating layer over said first conductive structure, said conductive structure having an opening with sidewalls and a bottom and exposes a portion of said first conductive structure;
providing a gas comprised of hydrogen incorporated within a plasma into said opening in said insulating layer; and
depositing a conductive material into said opening using chemical vapor deposition.
22. The method of claim 21, wherein said gas is additionally comprised of helium.
23. The method of claim 21, wherein said gas is additionally comprised of argon.
24. The method of claim 21, wherein said conductive material is comprised of a metal selected from the group consisting of: aluminum, copper, titanium, and a combination thereof.